

 <p>INFORMATION DISCLOSURE STATEMENT (Use Several Sheets if necessary)</p>	ATTY DOCKET NO.		APPLICATION NO.
	UTC 003		90/523,491
	APPLICANT		
	Klaus et al.		
FILING DATE		GROUP	
March 10, 2000		2811	

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

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OTHER DISCLOSURES (Including Author, Title, Date, Pertinent Pages, Place of Publication, Etc.)

EF	Kumagai et al., FABRICATION OF TITANIUM OXIDE THIN FILMS..., 1995, Thin Solid Films 263, pgs. 47-53
EF	Ritala et al., STUDIES ON THE MORPHOLOGY OF Al ₂ O ₃ THIN FILMS..., 1996, Thin Solid Films 286, pgs. 54-58
EF	Ritala et al., GROWTH OF TITANIUM DIOXIDE THIN FILMS..., 1993, Thin Solid Films 225, pgs. 288-295
EF	Han et al., A NEAR-EDGE X-RAY ABSORPTION FINE STRUCTURE STUDY OF ATOMIC LAYER EPITAXY..., 1998, Surface Science 415, pgs. 251-263
EF	Morishita et al., ATOMIC-LAYER CHEMICAL-VAPOR-DEPOSITION OF SILICON-NITRATE, 1997, Applied Surface Science 112, pgs. 198-204
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EF	Kumagai et al., TITANIUM OXIDE/ALUMINUM OXIDE MULTILAYER REFLECTORS..., May 1997, Applied Phys. Lett. 70 (18), pgs. 2338-2340

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EF	Kobayashi et al., IS SITU INFRARED REFLECTION AND TRANSMISSION ABSORBSION..., May 1993, Journal of Appl. Phys. 73 (9), pgs. 4637-4643
EF	Kobayashi et al., STUDY ON MECHANISM OF SELECTIVE CHEMICAL VAPOR DEPOSITION..., Jan. 1991, Journal of appl. Phys. 69 (2), pgs. 1013-1019
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